

MOSFET – Single, N-Channel, POWER TRENCH[®], 2.5 V Specified

30 V, 5.0 A, 40 mΩ

FDMA430NZ

General Description

This Single N-Channel MOSFET has been designed using onsemi's advanced POWER TRENCH process to optimize the $R_{DS(on)}$ @ $V_{GS} = 2.5$ V on special MicroFET[™] leadframe.

Features

- $R_{DS(on)} = 40$ mΩ at $V_{GS} = 4.5$ V, $I_D = 5.0$ A
- $R_{DS(on)} = 50$ mΩ at $V_{GS} = 2.5$ V, $I_D = 4.5$ A
- Low Profile – 0.8 mm Maximum in the New Package MicroFET 2x2 mm
- HBM ESD Protection Level > 2.5 kV Typical (Note 3)
- Free from Halogenated Compounds and Antimony Oxides
- This Device is Pb-Free, Halide Free and is RoHS Compliant

Applications

- Li-Ion Battery Pack

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

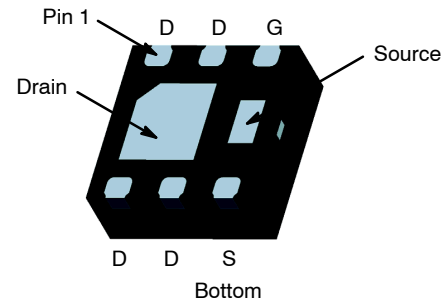
Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	±12	V
I_D	Drain Current – Continuous (Note 1a) – Pulsed	5.0 20	A
P_D	Power Dissipation (Steady State) – (Note 1a) – (Note 1b)	2.4 0.9	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

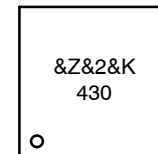
Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	145	

V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
30 V	40 mΩ @ 4.5 V	5.0 A
	50 mΩ @ 2.5 V	



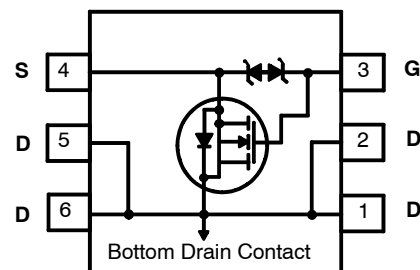
WDFN6 2x2, 0.65P
(MicroFET 2x2)
CASE 511CZ

MARKING DIAGRAM



&Z = Assembly Plant Code
&2 = 2-Digit Date Code
&K = 2-Digits Lot Run Traceability Code
430 = Specific Device Code

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping [†]
FDMA430NZ	WDFN6 (Pb-Free, Halide Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

FDMA430NZ

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain-Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	30	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C	–	25.2	–	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V	–	–	1	μA
I _{GSS}	Gate-Body Leakage	V _{GS} = ±12 V, V _{DS} = 0 V	–	–	±10	μA

ON CHARACTERISTICS (Note 2)

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	0.6	0.81	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C	–	–3.2	–	mV/°C
R _{DS(on)}	Static Drain-Source On Resistance	V _{GS} = 4.5 V, I _D = 5.0 A	–	23.6	40	mΩ
		V _{GS} = 4.0 V, I _D = 5.0 A	–	23.9	41	
		V _{GS} = 3.1 V, I _D = 4.5 A	–	25.4	43	
		V _{GS} = 2.5 V, I _D = 4.5 A	–	27.6	50	
		V _{GS} = 4.5 V, I _D = 5.0 A, T _J = 150°C	–	37.0	61	
g _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 5.0 A	–	25.6	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 10 V, V _{GS} = 0 V, f = 1.0 MHz	–	600	800	pF
C _{oss}	Output Capacitance		–	110	150	pF
C _{rss}	Reverse Transfer Capacitance		–	75	115	pF
R _G	Gate Resistance	f = 1.0 MHz	–	3.5	–	Ω

SWITCHING CHARACTERISTICS (Note 2)

t _{d(on)}	Turn-On Delay Time	V _{DD} = 10 V, I _D = 1 A, V _{GS} = 4.5 V, R _{GEN} = 6 Ω	–	8.3	17	ns
t _r	Turn-On Rise Time		–	7.1	15	ns
t _{d(off)}	Turn-Off Delay Time		–	18.1	37	ns
t _f	Turn-Off Fall Time		–	6.0	12	ns
Q _g	Total Gate Charge	V _{DS} = 10 V, I _D = 5.0 A, V _{GS} = 4.5 V	–	7.3	11	nC
Q _{gs}	Gate-Source Charge		–	0.8	2	nC
Q _{gd}	Gate-Drain Charge		–	1.9	3	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I _S	Maximum Continuous Drain–Source Diode Forward Current		–	–	2.0	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.0 A	–	0.69	1.2	V
t _{rr}	Diode Reverse Recovery Time	I _F = 5.0 A, di/dt = 100 A/μs	–	–	17	ns
Q _{rr}	Diode Reverse Recovery Charge		–	–	5	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.



a. 52°C/W when mounted
on a 1 in² pad of 2 oz copper



b. 145°C/W when mounted
on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

TYPICAL CHARACTERISTICS

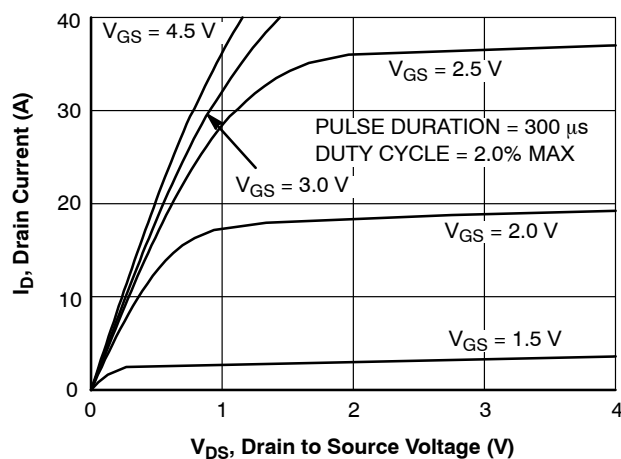
(T_J = 25°C unless otherwise noted)

Figure 1. On-Region Characteristics

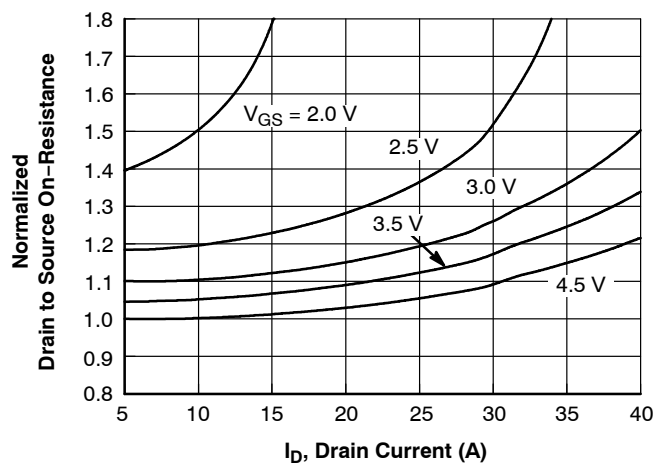


Figure 2. On-Resistance vs. Drain Current and Gate Voltage

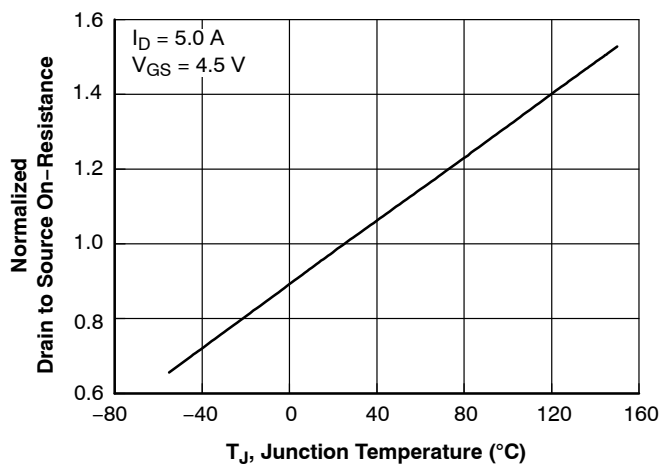


Figure 3. Normalized On-Resistance vs. Junction Temperature

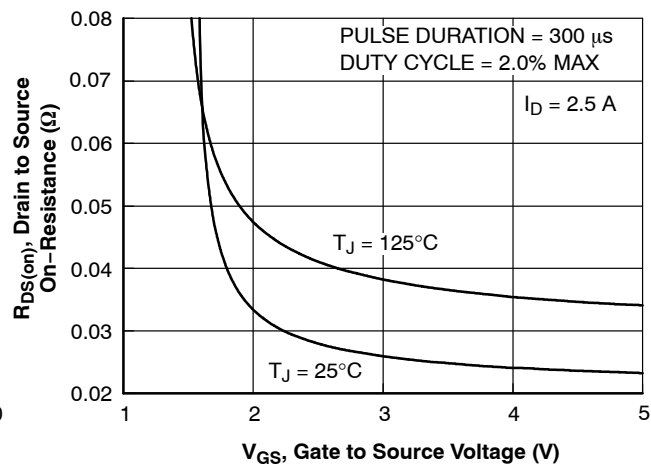


Figure 4. On-Resistance vs. Gate to Source Voltage

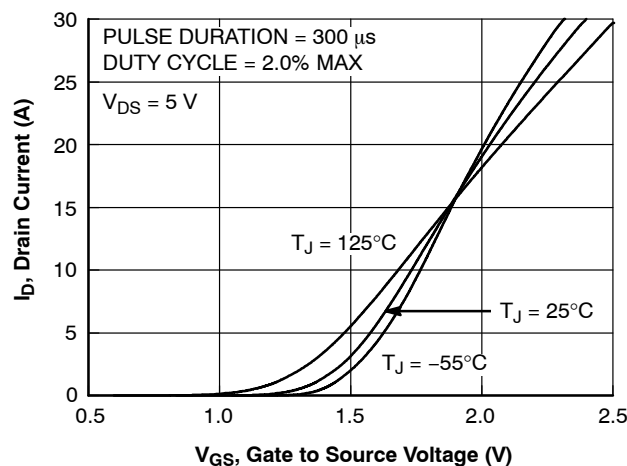


Figure 5. Transfer Characteristics

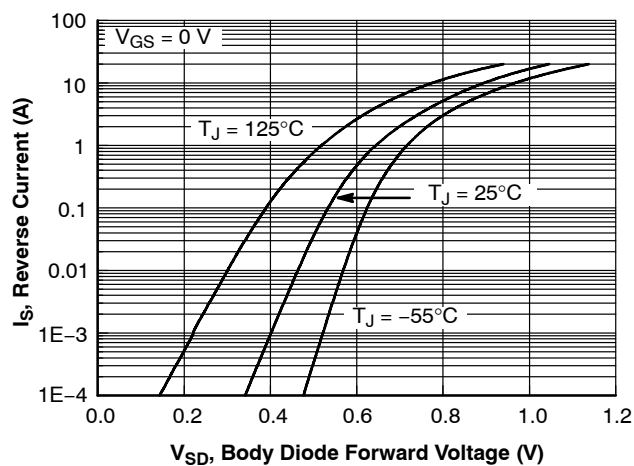


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

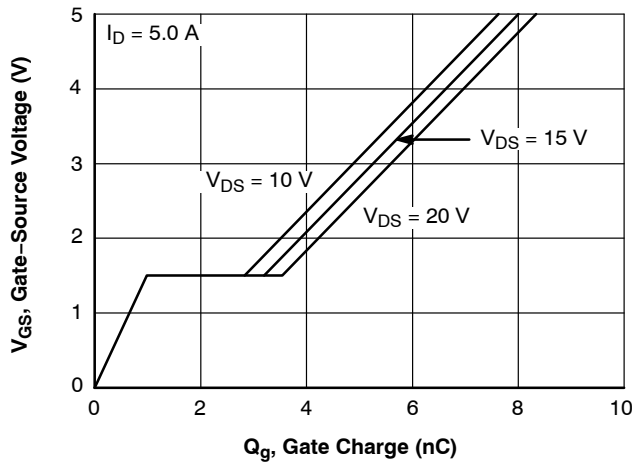


Figure 7. Gate Charge Characteristics

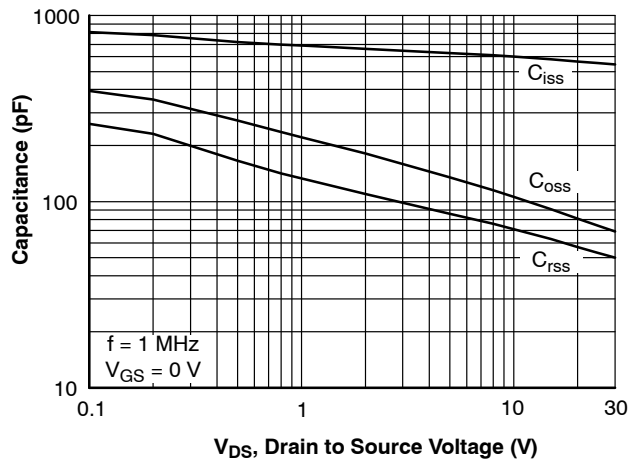


Figure 8. Capacitance vs. Drain to Source Voltage

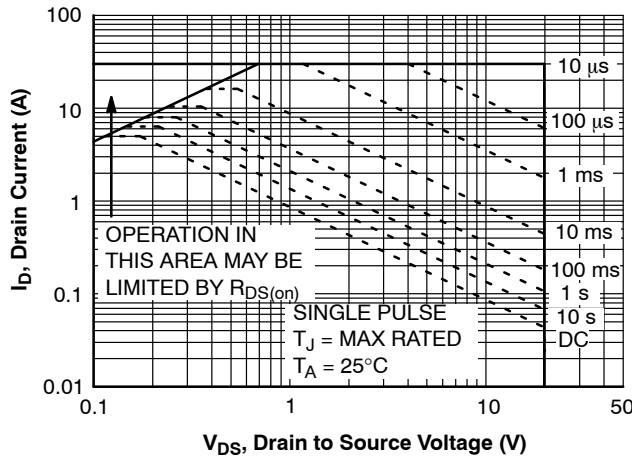


Figure 9. Safe Operating Area

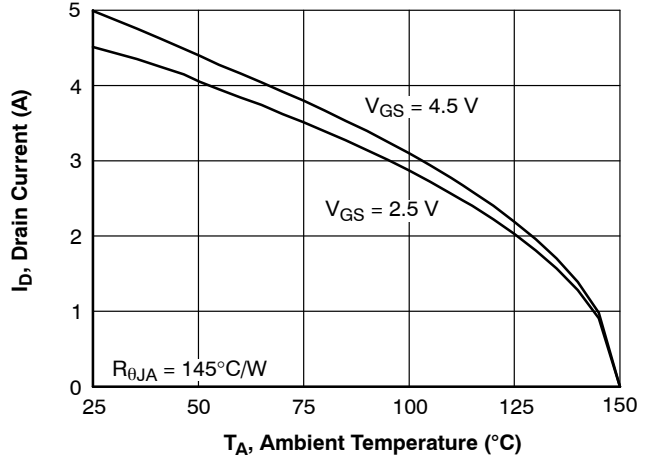


Figure 10. Maximum Continuous Drain Current vs. Ambient Temperature

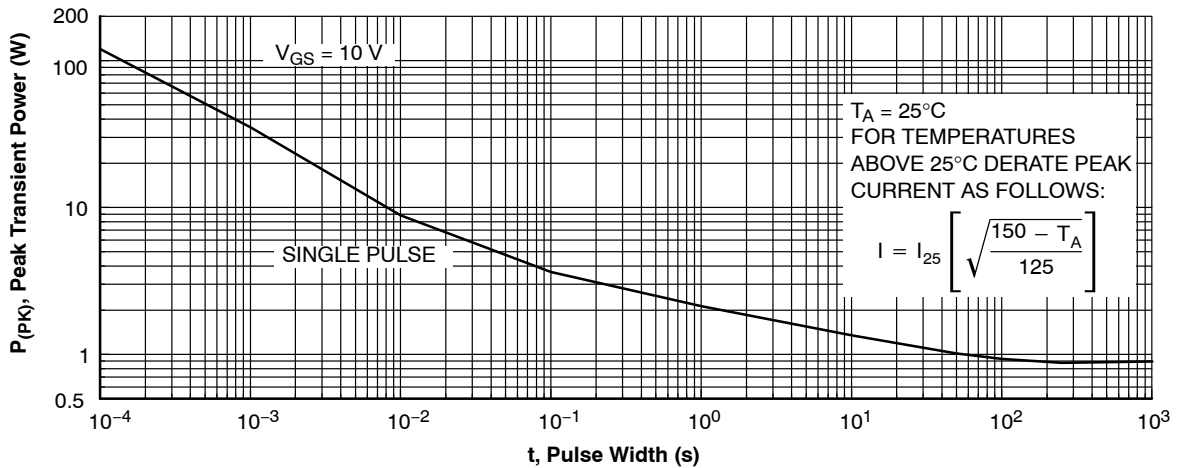


Figure 11. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (continued)

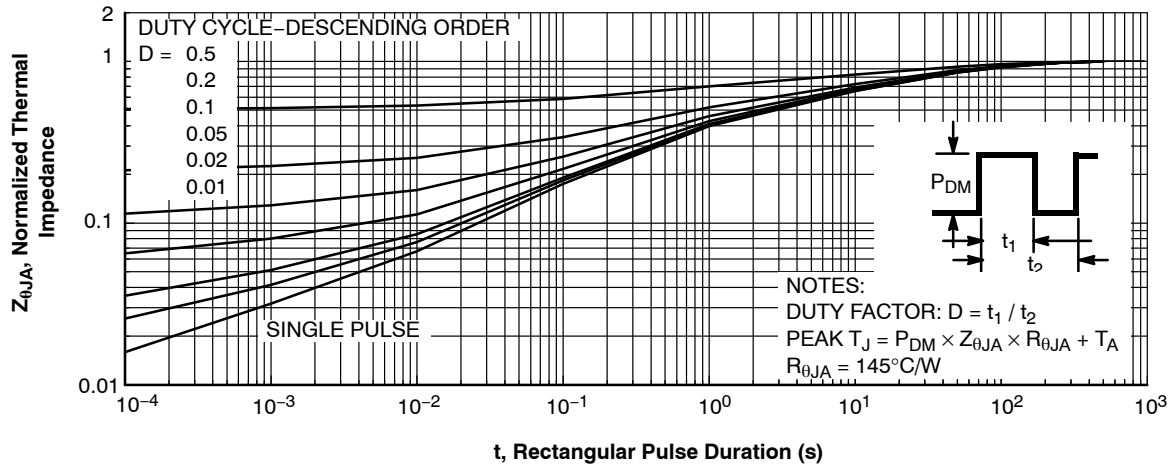
(T_J = 25°C unless otherwise noted)

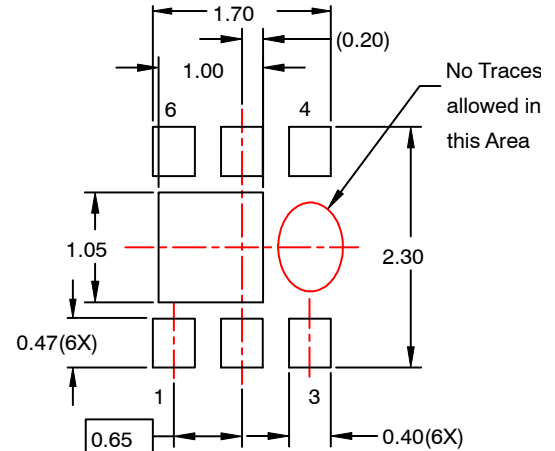
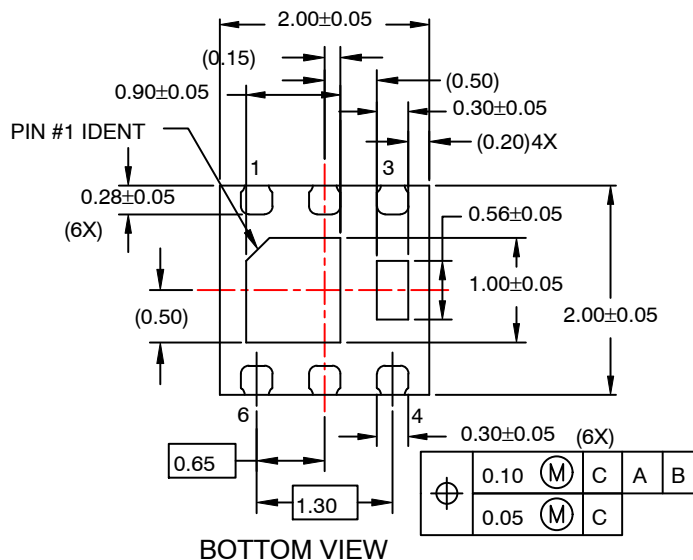
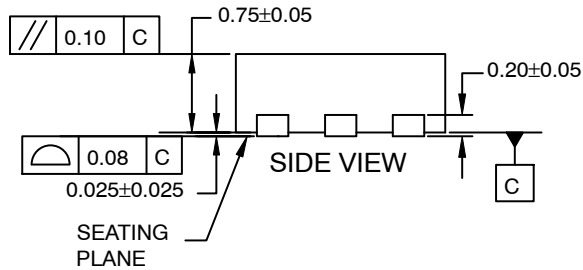
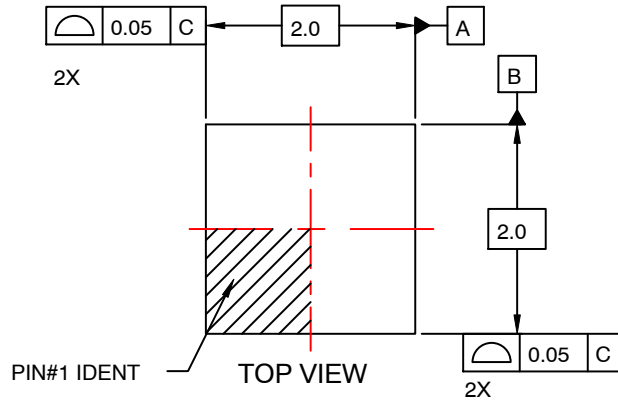
Figure 12. Transient Thermal Response Curve

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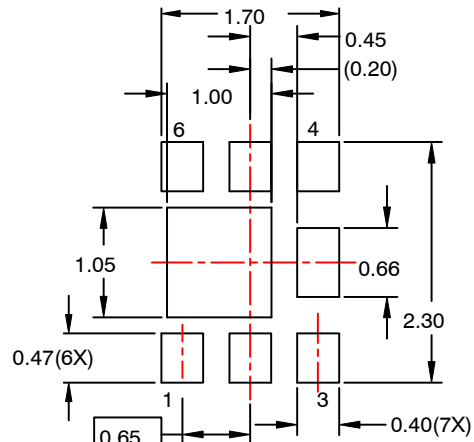
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WDFN6 2x2, 0.65P
CASE 511CZ
ISSUE O

DATE 31 JUL 2016



RECOMMENDED
LAND PATTERN OPT 1



RECOMMENDED
LAND PATTERN OPT 2

NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

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